

Ferromagnetic Curie point above room temperature in bulk ZnO

S. Banerjee^{a*}, M. Mandal^b, N. Gayathri^{c†} and M. Sardar^c

^a Surface Physics Division, ^b Chemical Science Division,

Saha Institute of Nuclear Physics, 1/AF Bidhannagar, Kolkata 700 064, India

^c Material Science Division, Indira Gandhi Center for Atomic Research, Kalpakkam 603 102, India

We report here observation of ferromagnetism in bulk ZnO. The ferromagnetic transition temperature T_c was observed to be above room temperature. The characterisation of the sample was carried out using XRD and SEM with EDAX. The results indicated that the sample is in pure ZnO phase and the size of the crystallites to be greater than 500 nm. We observe a finite coercive field upto 300K and a finite thermoremanent magnetization upto 340K. We also observe the green emission line (2.31eV, 535nm) in the photoluminescence (PL) spectra characteristic of singly ionised oxygen defects. We propose that the clustering of the paramagnetic singly ionised oxygen vacancies (V_O^\bullet) with a lone electron is responsible for the ferromagnetism in this system. Isolated paramagnetic vacancies give rise to a strong paramagnetic like behaviour below 10K.

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Ferromagnetism has been observed in a variety of doped wide band-gap semiconductors which has been generally known as dilute magnetic semiconductors (DMS)^{1,2}. Various mechanisms for the ferromagnetism in DMS systems has been proposed such as, percolation of bound magnetic polarons³, carrier induced ferromagnetism², donor impurity band exchange mediated by shallow donor electrons that form bound magnetic polaron⁴ etc. All the previous experimental observations of ferromagnetism in DMS has been seen in systems where there are transition metal (TM) dopants^{2,5,6,7,8,9,10,11,12,13,14,15,16,17}. The typical doping levels required for the observation of magnetism in these systems without destroying the semiconducting property is found to be $\approx 2\%$ to 5% . The ferromagnetism in these DMS systems has been attributed mainly to the transition metal dopants^{2,5,6,7,8,9,10,11,12,13,14,15,16,17}. Recently ferromagnetism has even been observed in undoped wide band gap semiconductor such as ZnO, HfO₂, SnO₂, In₂O₃, Al₂O₃, CeO₂ etc.^{18,19,20,21,22,23,24,25,26,27} in reduced dimensional form such as nanoparticle and thin films. Observation of ferromagnetism in these undoped systems created more excitement and threw open a wider debate as to the origin of magnetism in these wide band gap semiconductors. The ferromagnetism in these low dimensional systems has been attributed to oxygen defects and suggested as arising due to low dimensionality²⁶. This further raises questions whether the magnetism in the doped semiconductors is really due to the dopant or it is oxygen defect induced. The nature and specific organisation of the defects which can give rise to ferromagnetism is an important issue. Recently it has been shown that oxygen vacancy occurring in the O(3) sites in bulk Ga₂O₃ can give rise to ferromagnetism²⁸. In this

letter, observation of ferromagnetism in bulk ZnO which has not been observed before and a possible mechanism that we conjecture for the appearance of ferromagnetism in bulk ZnO is presented.

ZnO has a simple wurtzite structure where all oxygens and Zn sites are equivalent. We selected bulk ZnO for our investigation for magnetization measurement. The samples were prepared by miceller method using ZnSO₄ (1 m mol) and Sodium dodecyl sulphate (SDS) micelles (100 ml of 10^{-2} M). After thorough stirring and boiling 1 m mol NaOH in 1 ml aqueous solution was added slowly. Ethyl alcohol was added after refluxing the mixture for 1 hour and allowed to stand overnight. The precipitated ZnO white powder obtained after centrifuging was heated at 50°C for 24 hours to dry. This as prepared sample was annealed at 500°C and 900°C for 2 hours. The sample annealed at 900°C was light green in colour. The structural and chemical characterisation of the sample was carried out using XRD (Bruker) in the Bragg-Brentano geometry using CuK α emission line and SEM with EDAX (Philips FEI). The magnetic property was measured using MPMS-7 (Quantum Design). For the zero field cooled (ZFC) data, the sample was cooled down to 2K in the absence of magnetic field and the data was taken while warming up upto 340K in the presence of 100 Oe field. The field cooled data (FC) was taken while warming the sample after cooling it to 2K in the presence of the 100 Oe field. The hysteresis data were taken at 2K, 15K, 70K and 300K with field of 2000 Oe and 1 Tesla. The PL spectra was measured using Photoluminescence Spectrophotometer (Hitachi Model F-2500) to show the green luminescence signal.

The XRD of the sample annealed at 500°C showed the ZnO phase formation along with some peaks of the organic materials. No green photoluminescence (PL) signal was observed and a very weak ferromagnetic signal was observed (i.e., a small thermoremanent magnetisation and very low coercive field was observed). In this letter we will only present data for the sample annealed at 900°C as we are only interested to see the magnetic

*Email:sangambanerjee@hotmail.com

†Present address: Material Science Section, Variable Energy Cyclotron Center, 1/AF Bidhannagar, Kolkata 700 064, India

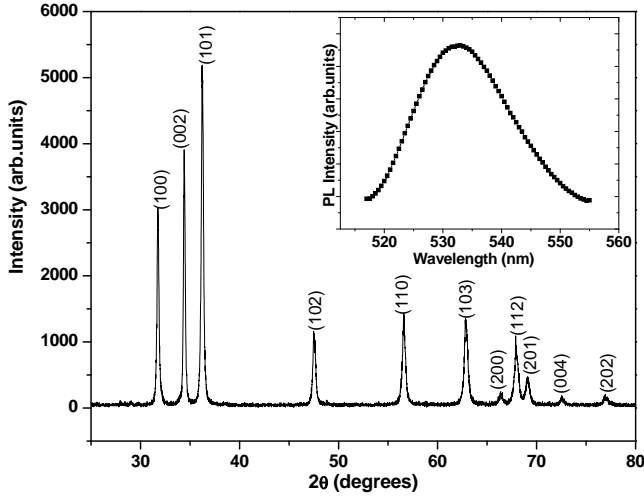


FIG. 1: X-ray diffraction pattern of the 900°C annealed sample. Inset: Photoluminescence spectra showing the broad green luminescence signal

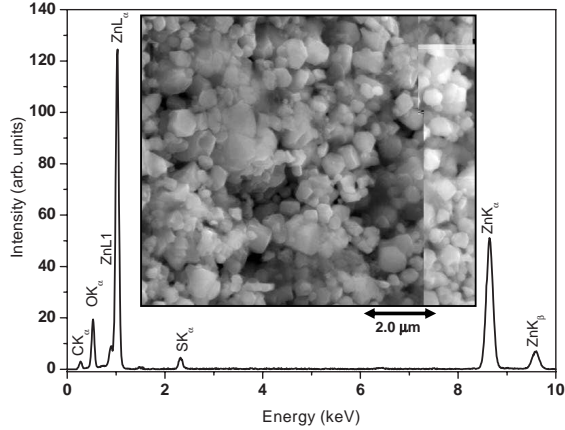


FIG. 2: EDAX spectra of the 900°C annealed sample showing no magnetic impurities. Inset: SEM micrograph showing the typical grain size > 500 nm

property of the bulk sample and the main focus of the paper is to look for the ferromagnetism in the bulk ZnO sample.

In fig. 1 we show the XRD of the 900°C annealed sample. The XRD confirms pure ZnO phase and the EDAX pattern shown in the fig. 2 shows that there are mainly Zn and O peaks with small signature of C and S as these elements were present in the chemicals used to prepare ZnO precipitate, apart from these elements no other (magnetic) elements could be detected. The SEM picture shown in inset of fig. 2 shows that particle size are typically greater than 500 nm. In the inset of fig. 1 we show the PL spectrum showing the distinct green luminescence peak at 535nm (2.31 eV).

Fig. 3 shows the ZFC and FC magnetisation curve taken at 100 Oe for the 900°C annealed sample. The dis-

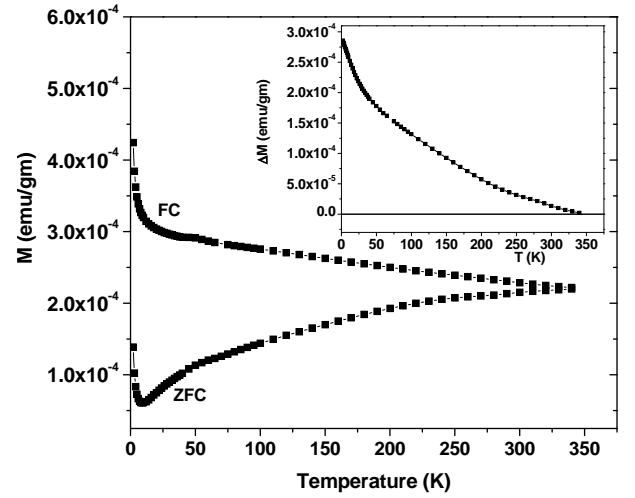


FIG. 3: ZFC and FC magnetisation curves of the 900°C annealed sample taken at 100 Oe field showing the distinct bifurcation above 340K. Inset: The thermoremanent magnetisation showing the finite value upto 340K.

tinct bifurcation of the FC and ZFC starts well above 340K which is also seen from the finite thermoremanent magnetisation in the inset of fig. 3 even at 340K. The ZFC magnetisation increases as a function of temperature for $T > 10$ K indicating that there are blocked moments which start contributing to the magnetisation when the temperature is increased. The FC magnetisation decreases as the temperature increases, since the frozen moments start randomizing due to thermal energy. This behaviour is seen in most DMS systems. It is interesting to note that there is a sharp increase in the magnetisation in both the FC and the ZFC data below 10K. The origin of this strong paramagnetic behaviour will be explained below.

In fig. 4 we show the (M vs. H) hysteresis curves of the sample at 4 different temperatures upto 2000 Oe after the necessary diamagnetic subtraction. We observe clear hysteresis at all temperatures upto 300K as seen in inset(a) of fig. 4. The inset(b) shows the hysteresis upto 1 Tesla showing non-saturation of the magnetisation at 2K. Magnetisation saturation can be observed for 300K.

The origin of ferromagnetism in this bulk ZnO can be explained invoking point defects. The intrinsic point defects could be either vacancies or interstitials. These can be either Zn or O defects. Various models have been proposed to explain the green emission which includes involvement of O vacancies^{29,30,31,32}, interstitial O^{33,34}, Zn vacancies and even Zn interstitials³⁵. Detailed first principle calculation of transition levels of these intrinsic point defect (vacancies and interstitials) in ZnO has been carried out extensively recently^{36,37,38,39}. There is no consensus on the nature of these transition levels, whether they are deep or shallow levels etc^{36,38,39}. It will be interesting to do more detailed calculation and compare the transition levels with experimental studies. Preparation of ZnO by chemical route (our method) will preferen-

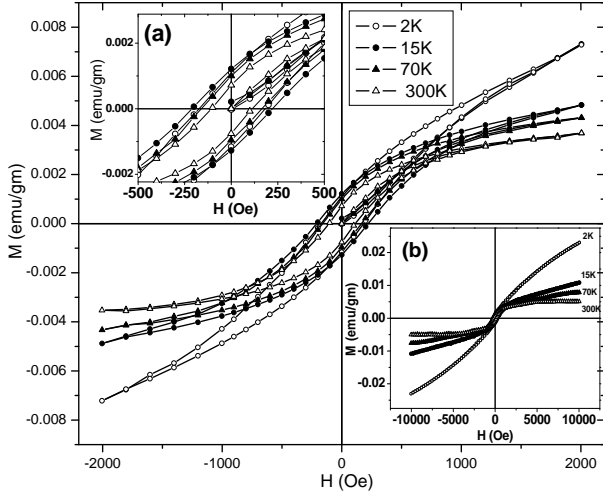


FIG. 4: M-H loops of the 900°C annealed sample at $T = 2\text{K}$, 15K, 70K and 300K upto 2000 Oe showing the non-saturation. Inset(a): Expanded low field region of the M-H loops showing the finite coersive field. Inset(b): M-H loops at the same temperatures upto 1 Tesla field showing saturation atleast at

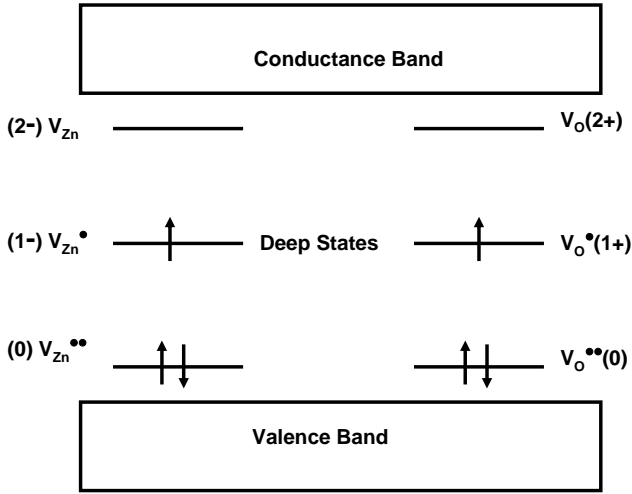


FIG. 5: Schematic diagram showing the positions of the energy levels of the Zn and O vacancies.

tially create vacancies rather than interstitials. The Zn vacancies in the ZnO can occur in three different charge states $V_{Zn}(2-)$, $V_{Zn}^\bullet(1-)$ and $V_{Zn}^{\bullet\bullet}(0)$. The oxygen vacancies in the ZnO can also occur in three different charge states $V_O(2+)$, $V_O^\bullet(1+)$ and $V_O^{\bullet\bullet}(0)$. The transitions levels of these vacancies can be schematically represented as shown in fig. 5.

The $V_O(2+)$ and the $V_{Zn}(2-)$ states form the shallow levels just below the conduction band minima. $V_O^{\bullet\bullet}(0)$ level and the $V_{Zn}^{\bullet\bullet}(0)$ forms the shallow level with 2 paired electrons just above the valence band maxima in the intrinsic band gap of ZnO. The singly charged $V_O^\bullet(1+)$ and $V_{Zn}^\bullet(1-)$ forms the deep level states with lone electron. The deep level states which has a lone electron are the

paramagnetic states in this system. The green luminescence seen in the PL spectrum can arise due to transition from these deep levels (lone electron levels) to the valence band. The magnetism seen in this bulk ZnO system can arise only due to these paramagnetic Zn and/or O vacancy states. Oxygen vacancies are likely to be more than the Zn vacancies because of the greater diffusivity of oxygen in general in the oxide systems. Recent theoretical calculation suggested that the oxygen vacancies with 0 and 2+ charge states displaces the surrounding Zn atoms causing finite local strain, whereas oxygen vacancy with 1+ charge state causes no local strain^{36,39}. This indicates that the 1+ charge state is the most favourable. This 1+ charge state oxygen vacancies are paramagnetic in nature because of the lone electron filling. Experimentally strong correlation between green luminescence intensity and paramagnetic oxygen defect concentration⁴⁰ is seen. Concentration of the paramagnetic oxygen defect is seen to be maximum at annealing temperature of 900°C. This strong correlation is also observed in the EPR measurements which only measures the paramagnetic moment signals^{40,41}. We observed no prominent green luminescence and very small thermoremanent magnetisation signal for the 500°C sample but observed a large prominent green luminescence signal and a significant thermoremanent magnetisation and finite hysteresis upto 300K for the 900°C sample.

One possible scenario that we conjecture for ferromagnetism is to assume that electrical conductivity takes place by tunneling from neutral to charged oxygen vacancies. The random field of charged oxygen vacancies, will produce a finite spread of the energy levels shown in Fig 5, of order $\frac{e^2}{\kappa R_A}$, where κ is the dielectric constant and R_A is the average separation of these vacancies. But nevertheless the motion of charges must be activated type due to large polaronic distortion of lattice around the neutral O vacancies. This activation should become smaller at lower temperatures. If we assume that the O vacancies organize themselves into clusters of nanosize, and the singly ionised O vacancy electrons are polarised (up spin as shown in Fig 5) then the down spin electron from neutral vacancy can easily delocalize within the vacancy cluster, because all the singly filled vacancies can accomodate it.

The various ways in which such ferro vacancy clusters can give rise to a ferromagnetic state, needs to be explored both experimentally and theoretically. The carrier concentration in ZnO is known to vary widely from $10^{15}/\text{cc}$ to $10^{17}/\text{cc}$ in bulk pellets^{42,43} to $10^{19}/\text{cc}$ in thin films⁴² depending on material preparation method. We do not have an independent estimate of carrier concentration in our sample, but assuming a carrier concentration of $10^{18}/\text{cc}$, and each carrier having a moment of $1\mu_B$, we get a moment of $2 \times 10^{-3} \text{ emu/gm}$ which is close to the saturation moment at $T=15\text{ K}$ and 2000 Oe of $4 \times 10^{-3} \text{ emu/gm}$ seen by us. It remains to be seen if the moment can be increased by an order of magnitude in thin film. Below 10K the ZFC and the FC thermo-magnetisation

data shows a sharp rise and these we attribute to isolated paramagnetic singly ionised oxygen vacancies (V_O^\bullet). Hence for low temperature (2K) hysteresis curve we see no tendency of saturation in the magnetisation even upto 1T as if a strong paramagnetic term dominates over the ferromagnetic term.

To summarise, we report here observation of ferromagnetism in bulk ZnO sample. The finite thermoremanent magnetization obtained from the difference between the ZFC and FC data upto 340K indicates that the ferromagnetic transition temperature T_c of the present bulk ZnO sample investigated to be above 340K. We observed a large prominent green luminescence signal from the sample and attributed it to the transitions from the deep lev-

els (paramagnetic singly ionised oxygen vacancies (V_O^\bullet) having lone electron levels) to the valence band. The paramagnetic singly ionised oxygen vacancies (V_O^\bullet) having lone electron levels forming clusters, these vacancies have ferromagnetic interactions and form ferromagnetic domains. Hence, we can conclude that the ferromagnetism and the green PL signal observed in the bulk ZnO sample arise from these paramagnetic singly ionised oxygen vacancies (V_O^\bullet).

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